Title (en)
METHOD OF FORMING NONVOLATILE MEMORIES WITH L-SHAPED FLOATING GATES

Title (de)
VERFAHREN ZUR HERSTELLUNG NICHTFLÜCHTIGER SPEICHER MIT L-FÖRMIGEN FLOATING GATES

Title (fr)
MÉTHODE DE FORMATION DE MÉMOIRES NON VOLATILES AVEC GRILLES FLOTTANTES EN FORME DE L

Publication
EP 2054925 A2 20090506 (EN)

Application
EP 07799975 A 20070802

Priority
- US 2007075041 W 20070802
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- US 46503806 A 20060816

Abstract (en)
[origin: WO2008021736A2] In a nonvolatile memory using floating gates to store charge, individual floating gates are L-shaped. Orientations of L-shaped floating gates may alternate in the bit line direction and may also alternate in the word line direction. L-shaped floating gates are formed by etching conductive portions using etch masks of different patterns to obtain floating gates of different orientations.

IPC 8 full level
H01L 21/28 (2006.01); **H01L 21/8247** (2006.01); **H01L 27/115** (2006.01); **H01L 29/423** (2006.01)

CPC (source: EP KR)
H01L 29/40114 (2019.07 - EP); **H01L 29/42324** (2013.01 - EP KR); **H01L 29/66825** (2013.01 - KR); **H10B 41/30** (2023.02 - EP KR); **H10B 41/35** (2023.02 - EP)

Citation (search report)
See references of WO 2008021736A2

Citation (examination)
US 2005199939 A1 20050915 - LUTZE JEFFREY W [US], et al

Designated contracting state (EPC)
AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HU IE IS IT LI LT LU LV MC MT NL PL PT RO SE SI SK TR

Designated extension state (EPC)
AL BA HR MK RS

DOCDB simple family (publication)
WO 2008021736 A2 20080221; **WO 2008021736 A3 20080807**; EP 2054925 A2 20090506; EP 2472570 A2 20120704; EP 2472570 A3 20130717; JP 2010501119 A 20100114; JP 5178721 B2 20130410; KR 101166563 B1 20120719; KR 20090077752 A 20090715; KR 20120041806 A 20120502; TW 200816396 A 20080401; TW I356472 B 20120111

DOCDB simple family (application)
US 2007075041 W 20070802; EP 07799975 A 20070802; EP 12162688 A 20070802; JP 2009524727 A 20070802; KR 20097004609 A 20070802; KR 20127007127 A 20070802; TW 96130025 A 20070814